

L Number	Hits	Search Text	DB	Time stamp
1	8	"error check and correction"	USPAT; EPO; JPO; DERWENT	2003/12/07 11:07
2	9	("error check and correction" or ECC) same (ECC adj2 memory adj2 cell adj2 array)	USPAT; EPO; JPO; DERWENT	2003/12/07 11:09
3	488	("error check and correction" or ECC) and (ECC adj2 memory)	USPAT; EPO; JPO; DERWENT	2003/12/07 11:09
4	9	("error check and correction" or ECC) and (ECC adj2 memory adj2 cell adj2 array)	USPAT; EPO; JPO; DERWENT	2003/12/07 11:09
5	9	(ECC adj2 memory adj2 cell adj2 array)	USPAT; EPO; JPO; DERWENT	2003/12/07 11:09
6	2	("error check and correction" or ECC) and (ECC adj2 memory) and wordlines and bitlines	USPAT; EPO; JPO; DERWENT	2003/12/07 11:10
7	16	("error check and correction" or ECC) and wordlines and bitlines	USPAT; EPO; JPO; DERWENT	2003/12/07 11:15
8	286	("error check and correction" or ECC) and ((word adj1 lines) or "WL") and ((bit adj1 lines) or "BL")	USPAT; EPO; JPO; DERWENT	2003/12/07 11:17
9	265	("error check and correction" or ECC) and ((word adj1 lines) or "WL") and ((bit adj1 lines) or "BL") and decod\$3	USPAT; EPO; JPO; DERWENT	2003/12/07 11:18
10	8	("error check and correction" or ECC) and ((word adj1 lines) or "WL") and ((bit adj1 lines) or "BL") and decod\$3 and (ECC adj2 memory adj2 cell\$1)	USPAT; EPO; JPO; DERWENT	2003/12/07 11:18
11	6	("error check and correction" or ECC) and ((word adj1 lines) or "WL") and ((bit adj1 lines) or "BL") and decod\$3 and (ECC adj2 memory adj2 cell\$1 adj2 array)	USPAT; EPO; JPO; DERWENT	2003/12/07 11:18
12	6	("error check and correction" or ECC) and ((word adj1 lines) or "WL") and ((bit adj1 lines) or "BL") and decod\$3 and (ECC adj2 memory adj2 cell\$1 adj2 array) and (semiconductor adj2 memory)	USPAT; EPO; JPO; DERWENT	2003/12/07 11:19
13	0	("error check and correction" or ECC) and ((word adj1 lines) or "WL") and ((bit adj1 lines) or "BL") and decod\$3 and (ECC adj2 memory adj2 cell\$1 adj2 array) and (semiconductor adj2 memory) and (normal adj2 memory adj2 cell\$1)	USPAT; EPO; JPO; DERWENT	2003/12/07 11:20
14	0	((word adj1 lines) or "WL") and ((bit adj1 lines) or "BL") and decod\$3 and (ECC adj2 memory adj2 cell\$1 adj2 array) and (semiconductor adj2 memory) and (normal adj2 memory adj2 cell\$1)	USPAT; EPO; JPO; DERWENT	2003/12/07 11:20
15	4	((word adj1 lines) or "WL") and ((bit adj1 lines) or "BL") and decod\$3 and (ECC adj2 memory adj2 cell\$1 adj2 array) and (semiconductor adj2 memory) and (normal adj2 memory)	USPAT; EPO; JPO; DERWENT	2003/12/07 11:20
17	10	(ECC adj2 memory) and (semiconductor adj2 memory) and (normal adj2 memory)	USPAT; EPO; JPO; DERWENT	2003/12/07 11:21
16	5	(ECC adj2 memory adj2 cell\$1 adj2 array) and (semiconductor adj2 memory) and (normal adj2 memory)	USPAT; EPO; JPO; DERWENT	2003/12/07 11:35
18	0	(ECC adj2 memory adj2 cell\$1) and (wordline\$1 adj2 decoder)	USPAT; EPO; JPO; DERWENT	2003/12/07 11:28
19	5	(ECC adj2 memory adj2 cell\$1) and ("X" adj2 decoder)	USPAT; EPO; JPO; DERWENT	2003/12/07 11:29

20	890	ECC and (semiconductor adj2 memory)	USPAT; EPO; JPO; DERWENT	2003/12/07 11:36
22	3300	("X" or "Y") adj decoder\$1	USPAT; EPO; JPO; DERWENT	2003/12/07 11:37
23	47839	((("X" or "Y") adj decoder\$1) and ((word adj1 line\$1) or "WL") or ((bit adj1 lines) or "BL"))	USPAT; EPO; JPO; DERWENT	2003/12/07 11:40
24	53706	decoder\$1 and ((word adj1 line\$1) or "WL") or ((bit adj1 lines) or "BL")	USPAT; EPO; JPO; DERWENT	2003/12/07 11:40
25	9729	decoder\$1 and ((word adj1 line\$1) or "WL") and ((bit adj1 lines) or "BL")	USPAT; EPO; JPO; DERWENT	2003/12/07 11:40
26	1166	((("X" or "Y") adj decoder\$1) and ((word adj1 line\$1) or "WL") and ((bit adj1 lines) or "BL"))	USPAT; EPO; JPO; DERWENT	2003/12/07 11:40
27	24	((("X" or "Y") adj decoder\$1) and ((word adj1 line\$1) or "WL") and ((bit adj1 lines) or "BL") and (ECC and (semiconductor adj2 memory))	USPAT; EPO; JPO; DERWENT	2003/12/07 11:40
28	29	((("X" or "Y") adj decoder\$1) and ((word adj1 line\$1) or "WL") and ((bit adj1 lines) or "BL") and ECC	USPAT; EPO; JPO; DERWENT	2003/12/07 11:49
29	38	ECC near4 memory near4 cell\$1 near4 array	USPAT; EPO; JPO; DERWENT	2003/12/07 11:50
30	8	ECC adj2 cell\$1 adj2 array	USPAT; EPO; JPO; DERWENT	2003/12/07 11:50
21	237	ECC same (semiconductor adj2 memory)	USPAT; EPO; JPO; DERWENT	2003/12/07 11:54
31	63	(ECC near5 design\$4) and (semiconductor adj2 memory)	USPAT; EPO; JPO; DERWENT	2003/12/07 11:59
32	18	ECC and (design near10 (semiconductor adj2 memory))	USPAT; EPO; JPO; DERWENT	2003/12/07 12:00
33	556	ECC and (error adj2 recovery)	USPAT; EPO; JPO; DERWENT	2003/12/07 12:01
34	14	ECC and (error adj2 recovery) and (semiconductor adj2 device)	USPAT; EPO; JPO; DERWENT	2003/12/07 12:04
35	493	(arrang\$5 or dispos\$5) near20 ECC	USPAT; EPO; JPO; DERWENT	2003/12/07 12:04
36	4	(arrang\$5 or dispos\$5) near20 (ECC adj4 cell\$1)	USPAT; EPO; JPO; DERWENT	2003/12/07 12:09
37	11	(arrang\$5 or dispos\$5) same (ECC adj4 cell\$1)	USPAT; EPO; JPO; DERWENT	2003/12/07 12:09

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11	6	("error check and correction" or ECC) and ((word adj1 lines) or "WL") and ((bit adj1 lines) or "BL") and decod\$3 and (ECC adj2 memory adj2 cell\$1 adj2 array)	USPAT; EPO; JPO; DERWENT	2003/12/07 11:18
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13	0	("error check and correction" or ECC) and ((word adj1 lines) or "WL") and ((bit adj1 lines) or "BL") and decod\$3 and (ECC adj2 memory adj2 cell\$1 adj2 array) and (semiconductor adj2 memory) and (normal adj2 memory adj2 cell\$1)	USPAT; EPO; JPO; DERWENT	2003/12/07 11:20
14	0	((word adj1 lines) or "WL") and ((bit adj1 lines) or "BL") and decod\$3 and (ECC adj2 memory adj2 cell\$1 adj2 array) and (semiconductor adj2 memory) and (normal adj2 memory adj2 cell\$1)	USPAT; EPO; JPO; DERWENT	2003/12/07 11:20
15	4	((word adj1 lines) or "WL") and ((bit adj1 lines) or "BL") and decod\$3 and (ECC adj2 memory adj2 cell\$1 adj2 array) and (semiconductor adj2 memory) and (normal adj2 memory)	USPAT; EPO; JPO; DERWENT	2003/12/07 11:20
17	10	(ECC adj2 memory) and (semiconductor adj2 memory) and (normal adj2 memory)	USPAT; EPO; JPO; DERWENT	2003/12/07 11:21
16	5	(ECC adj2 memory adj2 cell\$1 adj2 array) and (semiconductor adj2 memory) and (normal adj2 memory)	USPAT; EPO; JPO; DERWENT	2003/12/07 11:35
18	0	(ECC adj2 memory adj2 cell\$1) and (wordline\$1 adj2 decoder)	USPAT; EPO; JPO; DERWENT	2003/12/07 11:28
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27	24	((("X" or "Y") adj decoder\$1) and ((word adj1 line\$1) or "WL") and ((bit adj1 lines) or "BL") and (ECC and (semiconductor adj2 memory))	USPAT; EPO; JPO; DERWENT	2003/12/07 11:40
28	29	((("X" or "Y") adj decoder\$1) and ((word adj1 line\$1) or "WL") and ((bit adj1 lines) or "BL") and ECC	USPAT; EPO; JPO; DERWENT	2003/12/07 11:49
29	38	ECC near4 memory near4 cell\$1 near4 array	USPAT; EPO; JPO; DERWENT	2003/12/07 11:50
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34	14	ECC and (error adj2 recovery) and (semiconductor adj2 device)	USPAT; EPO; JPO; DERWENT	2003/12/07 12:04
35	493	(arrang\$5 or dispos\$5) near20 ECC	USPAT; EPO; JPO; DERWENT	2003/12/07 12:04
36	4	(arrang\$5 or dispos\$5) near20 (ECC adj4 cell\$1)	USPAT; EPO; JPO; DERWENT	2003/12/07 12:09
37	11	(arrang\$5 or dispos\$5) same (ECC adj4 cell\$1)	USPAT; EPO; JPO; DERWENT	2003/12/07 12:16
38	156	(arrang\$5 or dispos\$5) same (ECC adj4 circuit)	USPAT; EPO; JPO; DERWENT	2003/12/07 12:22
39	56	(arrang\$5 or dispos\$5) near10 (ECC adj4 circuit)	USPAT; EPO; JPO; DERWENT	2003/12/07 12:17
40	11	(arrang\$5 or dispos\$5) same (ECC adj4 cell\$1)	USPAT; EPO; JPO; DERWENT	2003/12/07 12:23
41	4	(arrang\$5 or dispos\$5) near10 (ECC adj4 cell\$1)	USPAT; EPO; JPO; DERWENT	2003/12/07 12:26
42	3496673	portion\$1 (ECC adj4 cell\$1)	USPAT; EPO; JPO; DERWENT	2003/12/07 12:27

44	5	portion\$1 same (ECC adj4 cell\$1)	USPAT; EPO; JPO; DERWENT	2003/12/07 12:27
43	4	portion\$1 near20 (ECC adj4 cell\$1)	USPAT; EPO; JPO; DERWENT	2003/12/07 12:42
45	48	(ECC adj1 mode)	USPAT; EPO; JPO; DERWENT	2003/12/07 12:48
46	796	(ECC adj3 memory)	USPAT; EPO; JPO; DERWENT	2003/12/07 12:48
47	221	(ECC adj1 memory)	USPAT; EPO; JPO; DERWENT	2003/12/07 12:49
48	4	(arrang\$5 or design\$5 or set\$4 or implemen\$4 or fabricat\$5) adj5 (ECC adj1 memory)	USPAT; EPO; JPO; DERWENT	2003/12/07 12:53
49	24	(arrang\$5 or design\$5 or set\$4 or implemen\$4 or fabricat\$5) near10 (ECC adj1 memory)	USPAT; EPO; JPO; DERWENT	2003/12/07 12:53